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Jc997 U.S. PTO
10/075588

02/15/02

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))			Docket No. OKI.306	
In Re Application Of: Hideaki MATSUHASHI et al.				
Serial No. NEW	Filing Date FEB. 15, 2002	Examiner TO BE ASSIGNED	Group Art Unit TO BE ASSIGNED	
Title: METHOD FOR MANUFACTURING FIELD EFFECT TRANSISTOR				
<p style="text-align: center;">Address to: Assistant Commissioner for Patents Washington, D.C. 20231</p> <p style="text-align: center;">37 CFR 1.97(b)</p> <p>1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.</p> <p style="text-align: center;">37 CFR 1.97(c)</p> <p>2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:</p> <p style="margin-left: 40px;"><input type="checkbox"/> the statement specified in 37 CFR 1.97(e);</p> <p style="text-align: center;">OR</p> <p style="margin-left: 40px;"><input type="checkbox"/> the fee set forth in 37 CFR 1.17(p).</p>				

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No. OKI.306

In Re Application: Hideaki MATSUHASHI et al.

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Serial No.
NEW

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FEB. 15, 2002

Examiner
TO BE ASSIGNED

Group Art Unit
TO BE ASSIGNED

METHOD FOR MANUFACTURING FIELD EFFECT TRANSISTOR

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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Dated: FEB. 15, 2002

ADAM C. VOLENTINE
REG. NO. 33289

VOLENTINE FRANCOS, PLLC
12200 SUNRISE VALLEY DRIVE, SUITE 150
RESTON, VA 20191

TEL. NO. (703) 715-0870

CC:

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

OKI.306

Application Number

NEW

Applicant(s)

Hideaki MATSUHASHI et al.

Filing Date

FEB. 15, 2002

Group Art Unit

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	A	Terukazu Ohno et al., "Experimental 0.25-um-Gate Fully Depleted CMOS/SIMOX Process Using a New Two-Step LOCOS Isolation Technique," IEE Transactions on Electron Devices, Vol. 42, No. 8, August 1995.
	B	T. Naka et al., "A 0.35um Shallow SIMOX/CMOS Technology for Low-Power, High-Speed Applications," The Institute of Electronics, Information and Communication Engineers, Technical Report of IEICE (1997-03), page 45-52.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.